



No.3817

2SJ232

P-Channel MOS Silicon FET

Very High-Speed
Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Its height onboard is 9.5mm.
- Meets radial taping.

Absolute Maximum Ratings at Ta = 25°C

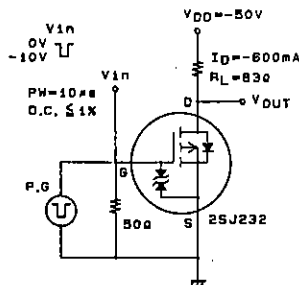
			unit
Drain to Source Voltage	V _{DS}	-100	V
Gate to Source Voltage	V _{GSS}	±15	V
Drain Current(DC)	I _D	-1.2	A
Drain Current(Pulse)	I _{DP}	-4.8	A
Allowable Power Dissipation	P _D	1.5	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

PW ≤ 10μs, duty cycle ≤ 1%

Electrical Characteristics at Ta = 25°C

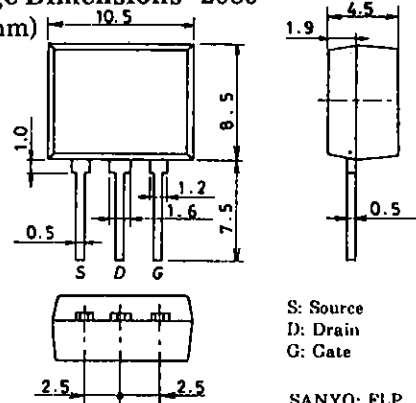
			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D = -1mA, V _{GS} = 0	-100			V
G-S Breakdown Voltage	V _{(BR)GSS}	I _G = ±100μA, V _{DS} = 0	±15			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -100V, V _{GS} = 0			-100	μA
Gate to Source Leakage Current	I _{GSS}	V _{GS} = ±12V, V _{DS} = 0			±10	μA
Cutoff Voltage	V _{GS(off)}	V _{DS} = -10V, I _D = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} = -10V, I _D = -600mA	0.9	1.6		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D = -600mA, V _{GS} = -10V		0.7	0.95	Ω
	R _{DS(on)}	I _D = -600mA, V _{GS} = -4V		0.95	1.3	Ω
Input Capacitance	C _{iss}	V _{DS} = -20V, f = 1MHz		380		pF
Output Capacitance	C _{oss}	V _{DS} = -20V, f = 1MHz		100		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} = -20V, f = 1MHz		20		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		12		ns
Rise Time	t _r	∕		14		ns
Turn-OFF Delay Time	t _{d(off)}	∕		85		ns
Fall Time	t _f	∕		40		ns
Diode Forward Voltage	V _{SD}	I _S = -1.2 A, V _{GS} = 0	-1.0	-1.5		V

Switching Time Test Circuit



Package Dimensions 2085

(unit : mm)

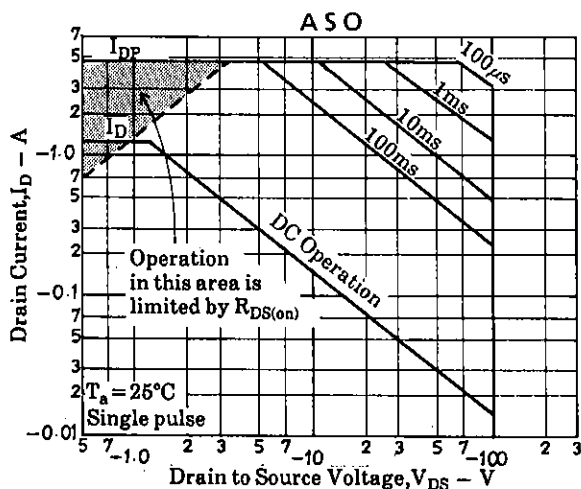
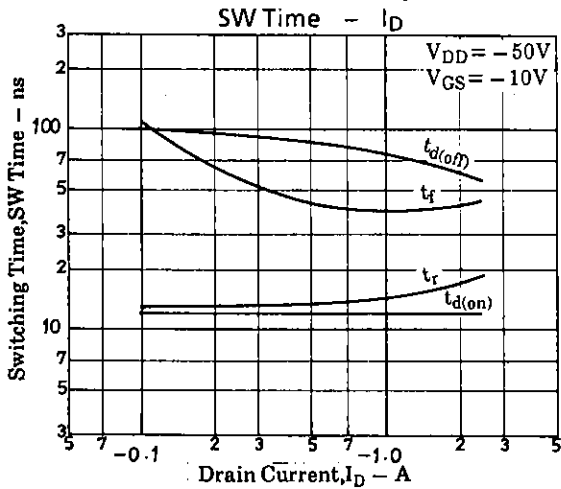
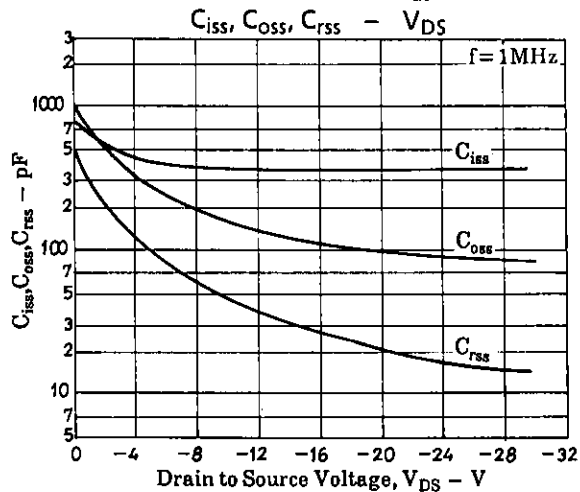
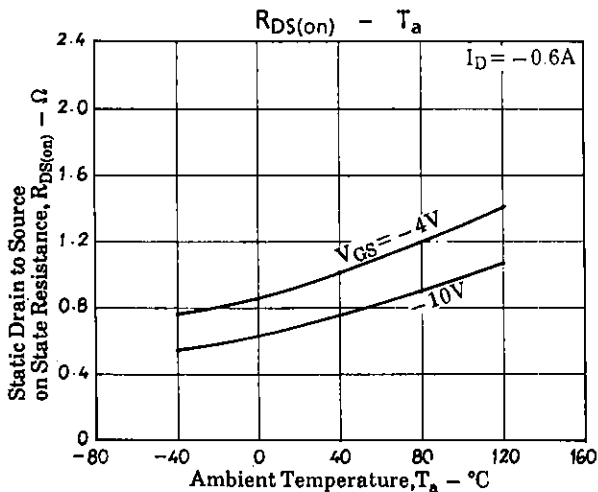
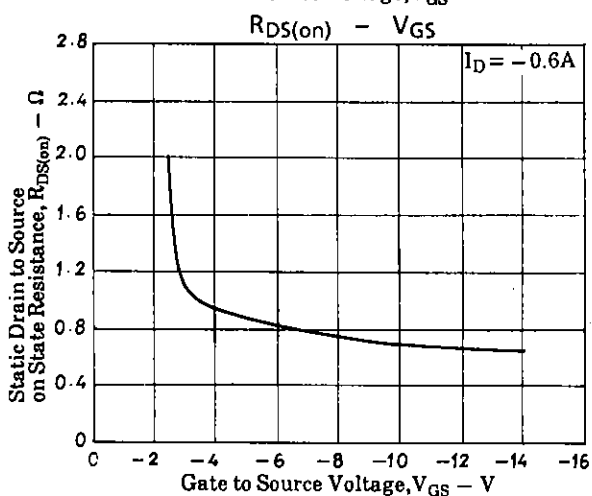
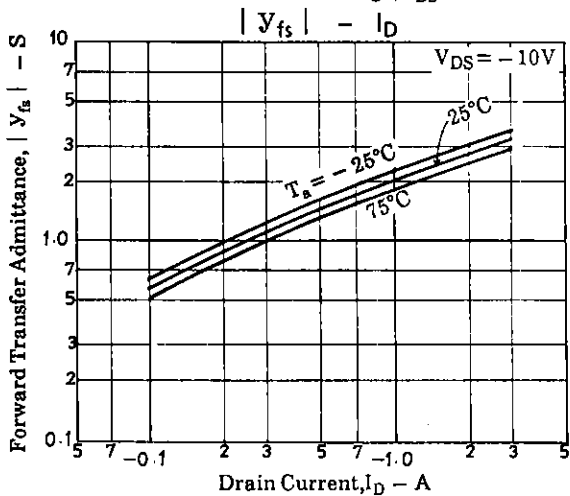
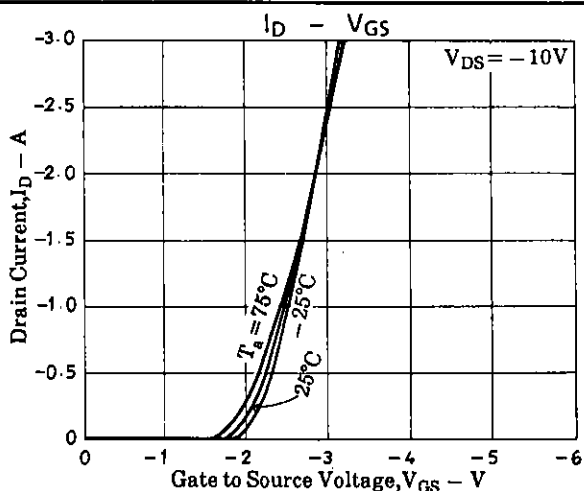
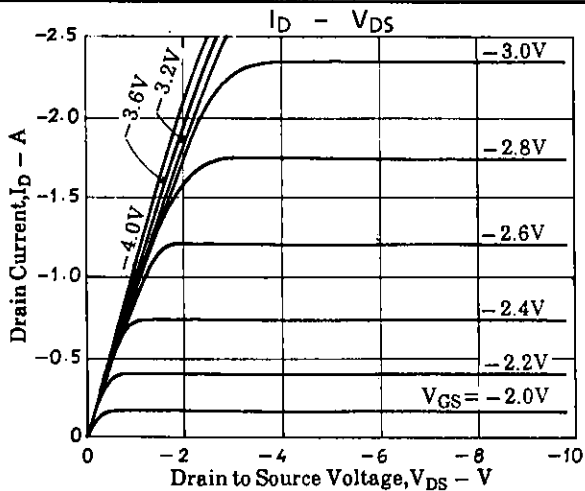


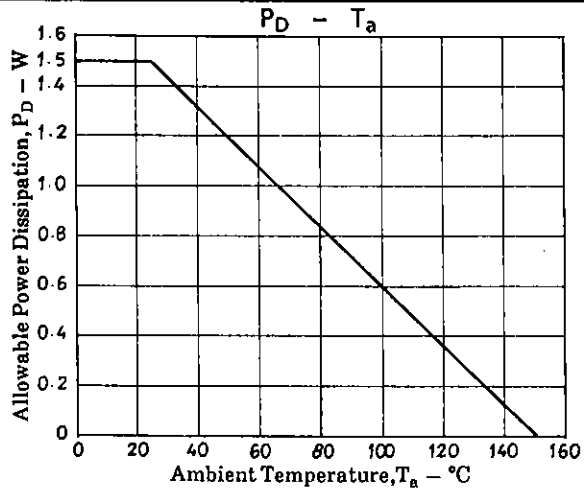
S: Source
D: Drain
G: Gate

SANYO: FLP

SANYO Electric Co., Ltd. Semiconductor Business Headquarters

TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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